

1 ABSTRACT OF THE DISCLOSURE

2 In one aspect, the invention encompasses a method of utilizing a
3 vaporization surface as an electrode to form a plasma within a vapor
4 forming device. In another aspect, the invention encompasses a method
5 of chemical vapor deposition. A vaporization surface is provided and
6 heated. At least one material is flowed past the heated surface to
7 vaporize the material. A deposit forms on the vaporization surface
8 during the vaporization. The vaporization surface is then utilized as an
9 electrode to form a plasma, and at least a portion of the deposit is
10 removed with the plasma. In another aspect, the invention encompasses
11 a vapor forming device. Such device includes a non-vapor-state-material
12 input region, a vaporization surface, and a flow path between the non-
13 vapor-state-material input region and the vaporization surface. The
14 device further includes a vapor-state-material output region, and a vapor
15 flow path from the vaporization surface to the vapor-state-material output
16 region. Additionally, the device includes a first plasma electrode spaced
17 from the vaporization surface, and plasma generation circuitry configured
18 to utilize the vaporization surface as a second plasma electrode such that
19 a plasma can be formed between the first and second plasma electrodes.
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